



STD1NA60

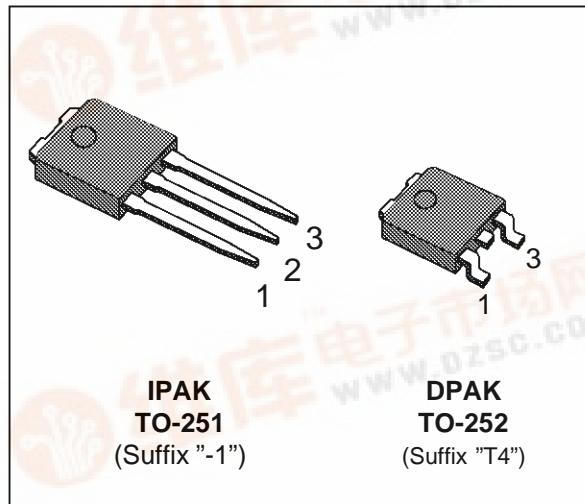
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|----------|------------------|---------------------|----------------|
| STD1NA60 | 600 V | < 8 Ω | 1.6 A |

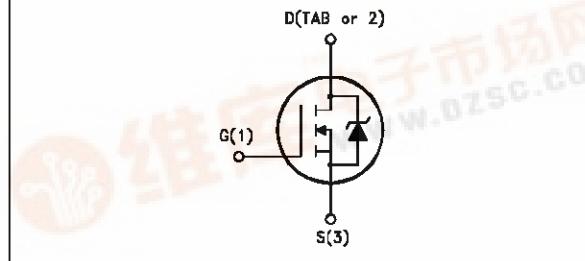
- TYPICAL R_{DS(on)} = 7.2 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

APPLICATIONS

- HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- MOTOR CONTROL, AUDIO AMPLIFIERS
- INDUSTRIAL ACTUATORS
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT
- PARTICULARLY SUITABLE FOR ELECTRONIC FLUORESCENT LAMP BALLASTS



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|--------------------|---|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 600 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 600 | V |
| V _{GS} | Gate-source Voltage | ± 30 | V |
| I _D | Drain Current (continuous) at T _c = 25 °C | 1.6 | A |
| I _D | Drain Current (continuous) at T _c = 100 °C | 1 | A |
| I _{DM(•)} | Drain Current (pulsed) | 6.4 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 40 | W |
| | Derating Factor | 0.32 | W/°C |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(•) Pulse width limited by safe operating area

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THERMAL DATA

| | | | | |
|----------------|--|-----|------|------|
| $R_{thj-case}$ | Thermal Resistance Junction-case | Max | 3.12 | °C/W |
| $R_{thj-amb}$ | Thermal Resistance Junction-ambient | Max | 100 | °C/W |
| $R_{thj-amb}$ | Thermal Resistance Case-sink | Typ | 1.5 | °C/W |
| T_J | Maximum Lead Temperature For Soldering Purpose | | 275 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|----------|--|-----------|------|
| I_{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$) | 1.6 | A |
| E_{AS} | Single Pulse Avalanche Energy (starting $T_j = 25$ °C, $I_D = I_{AR}$, $V_{DD} = 50$ V) | 13 | mJ |
| E_{AR} | Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$) | 0.5 | mJ |
| I_{AR} | Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100$ °C, pulse width limited by T_j max, $\delta < 1\%$) | 1 | A |

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|-----------|----------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage | $I_D = 250$ μA $V_{GS} = 0$ | 600 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{GS} = 0$) | $V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125$ °C | | | 25 250 | μA μA |
| I_{GSS} | Gate-body Leakage Current ($V_{DS} = 0$) | $V_{GS} = \pm 30$ V | | | ± 100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-----------------------------------|---|------|------|------|------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}$ $I_D = 250$ μA | 2.25 | 3 | 3.75 | V |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10$ V $I_D = 1$ A | | 7.2 | 8 | Ω |
| $I_{D(on)}$ | On State Drain Current | $V_{DS} > I_{D(on)} \times R_{DS(on)\max}$ $V_{GS} = 10$ V | 1 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|------------------------------|--|------|------|------|------|
| $g_{fs} (*)$ | Forward Transconductance | $V_{DS} > I_{D(on)} \times R_{DS(on)\max}$ $I_D = 1$ A | 0.65 | 1.2 | | S |
| C_{iss} | Input Capacitance | $V_{DS} = 25$ V $f = 1$ MHz $V_{GS} = 0$ | | 230 | 300 | pF |
| C_{oss} | Output Capacitance | | | 42 | 55 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 10 | 15 | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|--|------|--------------|----------|------------------|
| $t_{d(on)}$ t_r | Turn-on Time Rise Time | $V_{DD} = 300 \text{ V}$ $I_D = 1 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 3) | | 8 13 | 12 20 | ns ns |
| $(di/dt)_{on}$ | Turn-on Current Slope | $V_{DD} = 480 \text{ V}$ $I_D = 2 \text{ A}$ $R_G = 47 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 5) | | 180 | | A/ μs |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 480 \text{ V}$ $I_D = 2 \text{ A}$ $V_{GS} = 10 \text{ V}$ | | 15 5 6 | 25 | nC nC nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------------------|---|--|------|--------------|----------------|----------------|
| $t_{r(voff)}$ t_f t_c | Off-voltage Rise Time Fall Time Cross-over Time | $V_{DD} = 480 \text{ V}$ $I_D = 2 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 5) | | 8 15 8 | 12 25 12 | ns ns ns |

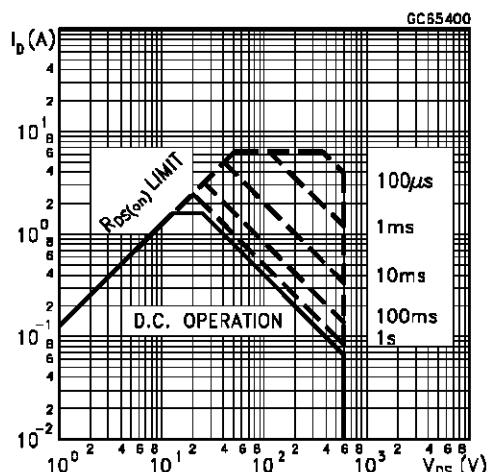
SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|----------------|------------|--------------------------|
| I_{SD} $I_{SDM}(\bullet)$ | Source-drain Current Source-drain Current (pulsed) | | | | 1.6 6.4 | A A |
| $V_{SD} (\ast)$ | Forward On Voltage | $I_{SD} = 1.6 \text{ A}$ $V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 2 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100 \text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, figure 5) | | 400 4 20 | | ns μC A |

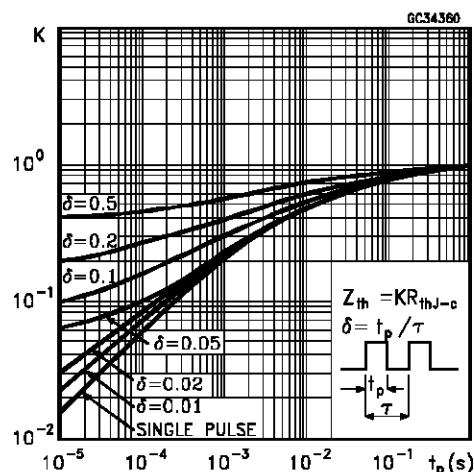
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(*) Pulse width limited by safe operating area

Safe Operating Area

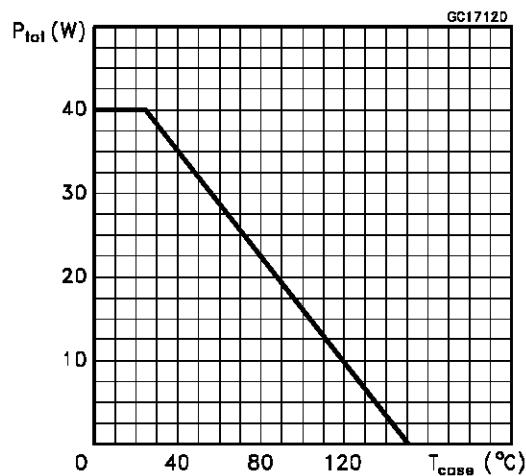


Thermal Impedance

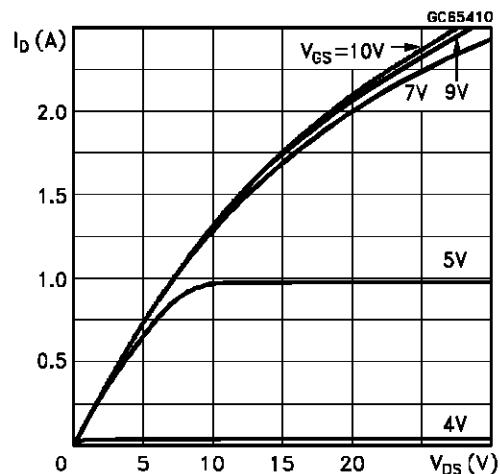


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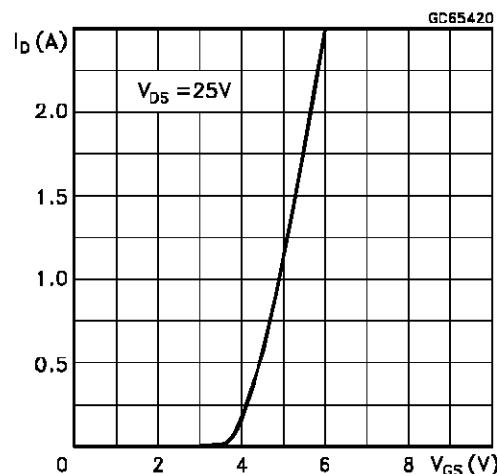
Derating Curve



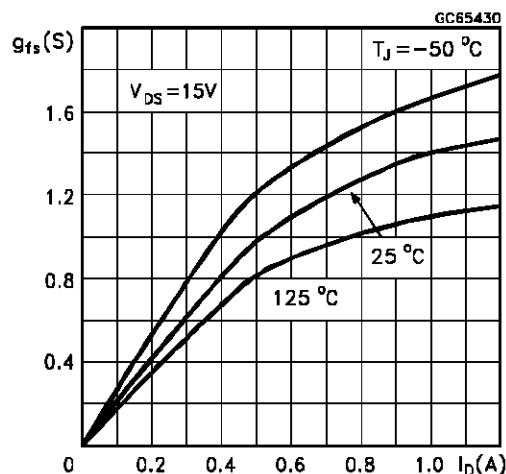
Output Characteristics



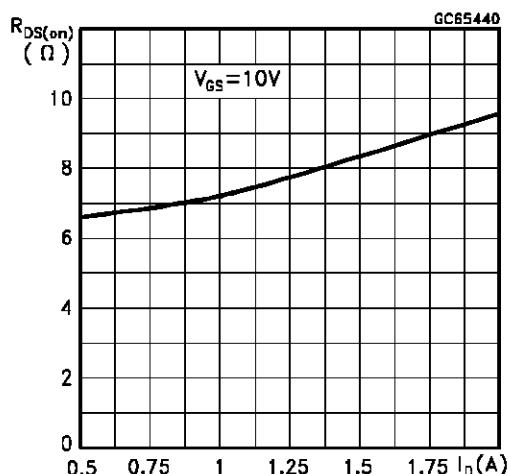
Transfer Characteristics



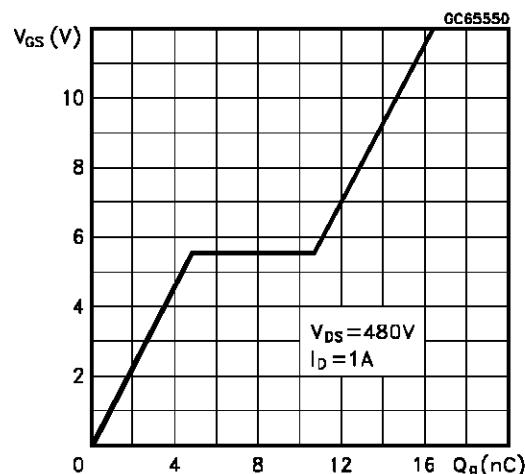
Transconductance



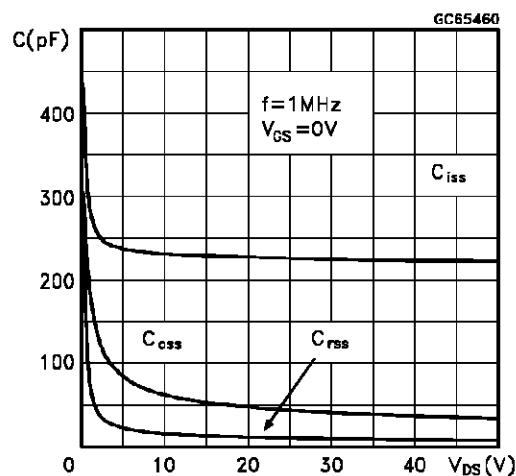
Static Drain-source On Resistance



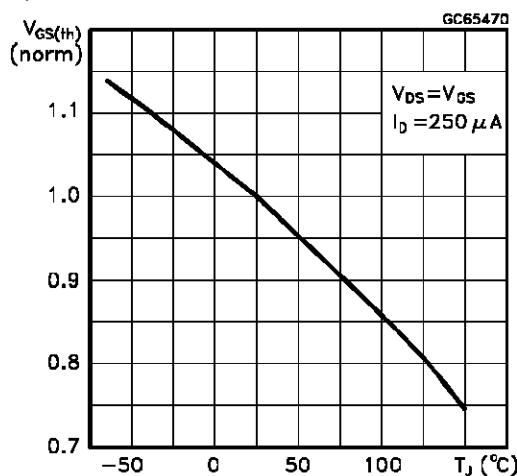
Gate Charge vs Gate-source Voltage



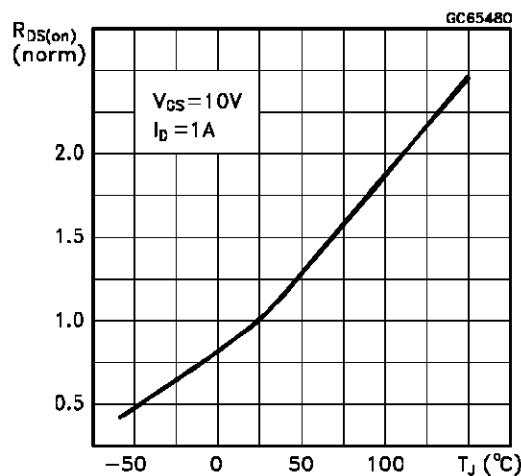
Capacitance Variations



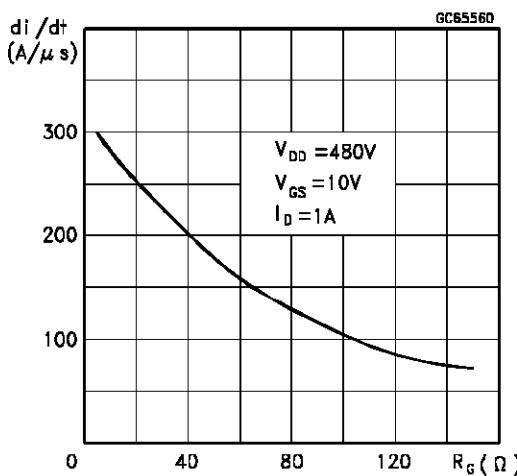
Normalized Gate Threshold Voltage vs Temperature



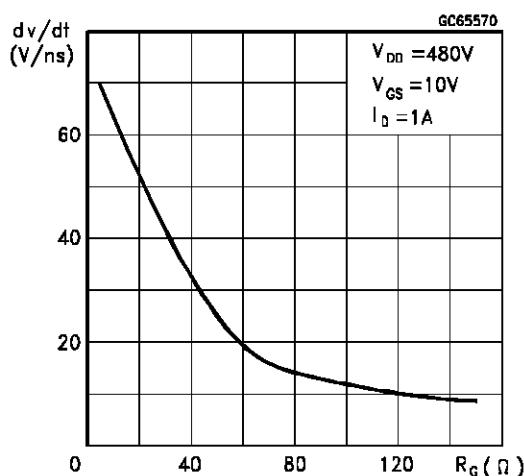
Normalized On Resistance vs Temperature



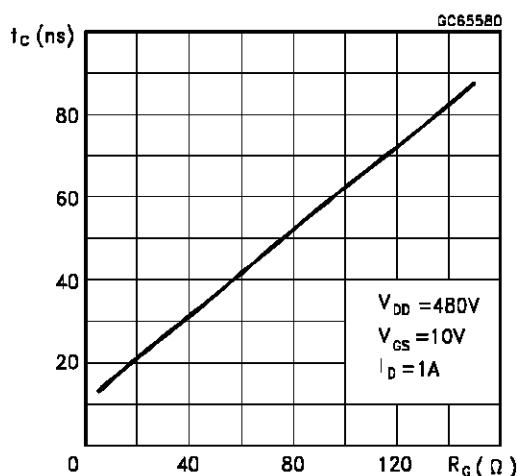
Turn-on Current Slope



Turn-off Drain-source Voltage Slope

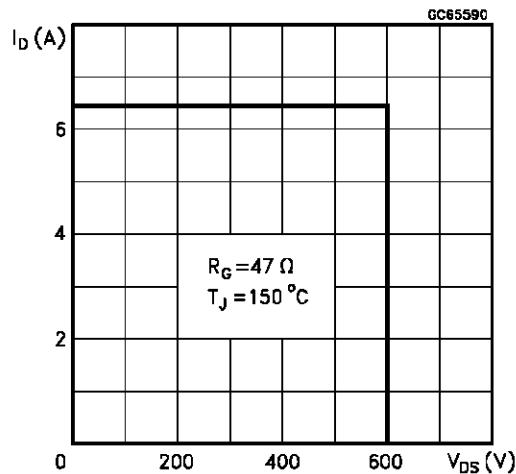


Cross-over Time

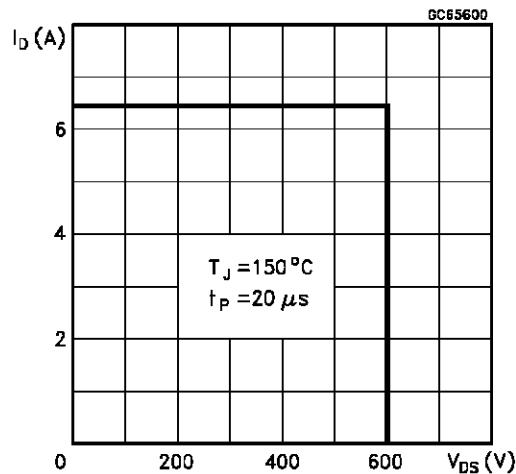


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Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

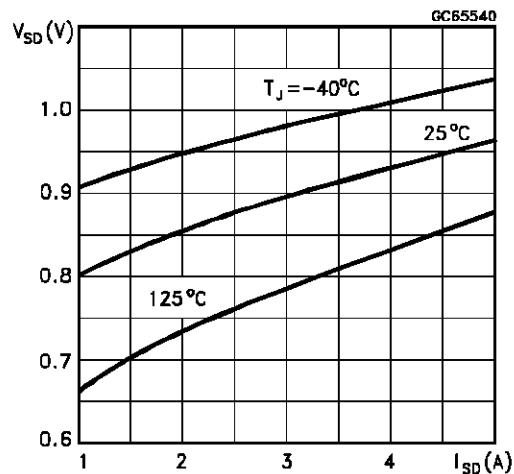


Fig. 1: Unclamped Inductive Load Test Circuits

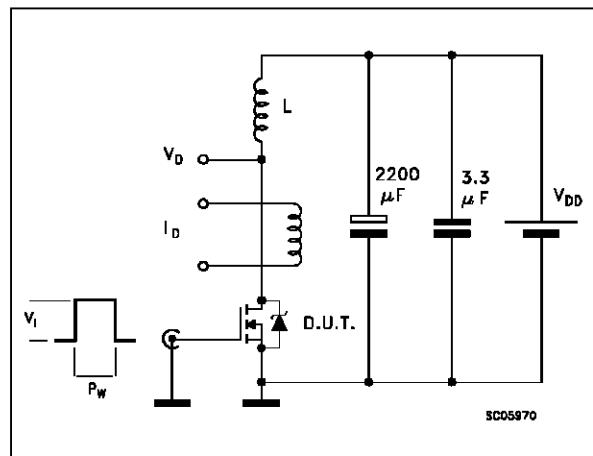


Fig. 2: Unclamped Inductive Waveforms

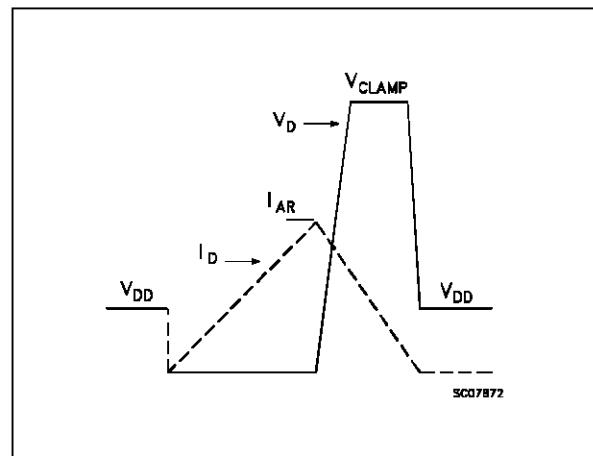


Fig. 3: Switching Times Test Circuits For Resistive Load

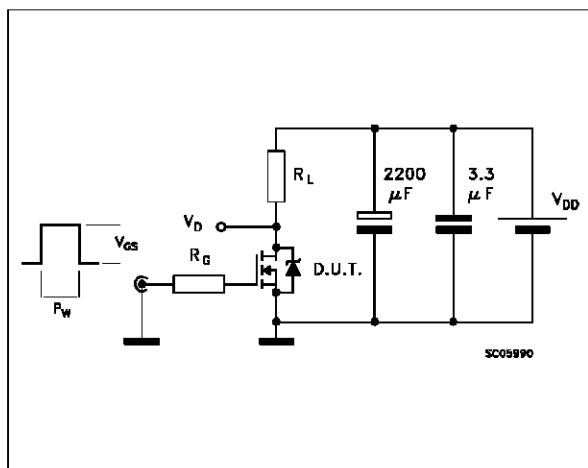


Fig. 4: Gate Charge Test Circuit

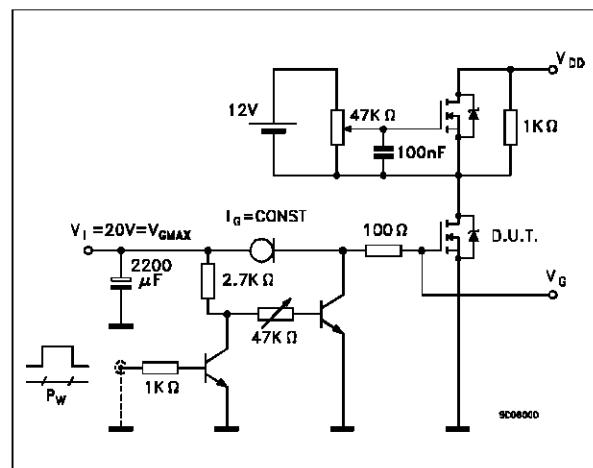
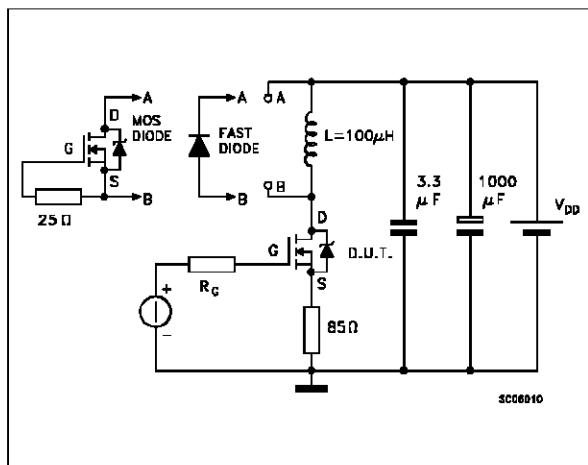
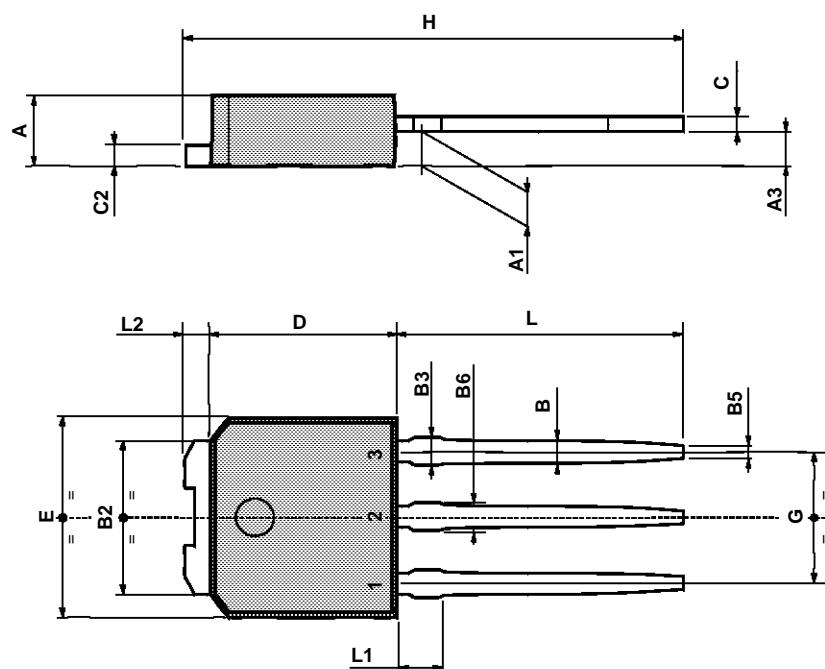


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-251 (IPAK) MECHANICAL DATA

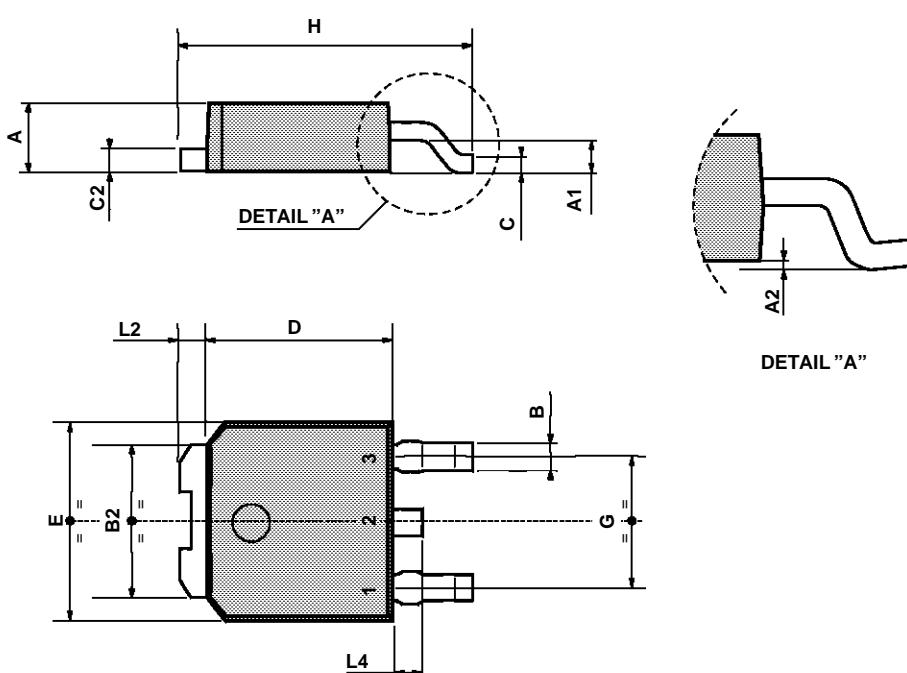
| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A3 | 0.7 | | 1.3 | 0.027 | | 0.051 |
| B | 0.64 | | 0.9 | 0.025 | | 0.031 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| B3 | | | 0.85 | | | 0.033 |
| B5 | | 0.3 | | | 0.012 | |
| B6 | | | 0.95 | | | 0.037 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 15.9 | | 16.3 | 0.626 | | 0.641 |
| L | 9 | | 9.4 | 0.354 | | 0.370 |
| L1 | 0.8 | | 1.2 | 0.031 | | 0.047 |
| L2 | | 0.8 | 1 | | 0.031 | 0.039 |



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TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.9 | 0.025 | | 0.035 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 9.35 | | 10.1 | 0.368 | | 0.397 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.6 | | 1 | 0.023 | | 0.039 |



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